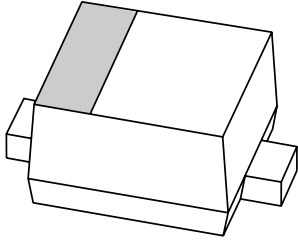


DATA SHEET



BAS516 High-speed diode

Product data sheet

1998 Aug 31

High-speed diode

BAS516

FEATURES

- Ultra small plastic SMD package
- High switching speed: max. 4 ns
- Continuous reverse voltage: max. 75 V
- Repetitive peak reverse voltage: max. 85 V
- Repetitive peak forward current: max. 500 mA.

APPLICATIONS

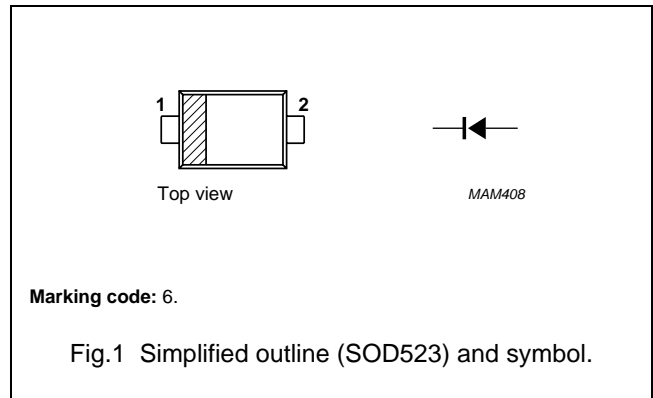
- High-speed switching in e.g. surface mounted circuits.

DESCRIPTION

The BAS516 is a high-speed switching diode fabricated in planar technology, and encapsulated in the SOD523 (SC79) SMD plastic package.

PINNING

PIN	DESCRIPTION
1	cathode
2	anode



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{RRM}	repetitive peak reverse voltage		–	85	V
V_R	continuous reverse voltage		–	75	V
I_F	continuous forward current	$T_s = 90\text{ °C}$; note 1; see Fig.2	–	250	mA
I_{FRM}	repetitive peak forward current		–	500	mA
I_{FSM}	non-repetitive peak forward current	square wave; $T_j = 25\text{ °C}$ prior to surge; see Fig.4 $t = 1\ \mu\text{s}$ $t = 1\ \text{ms}$ $t = 1\ \text{s}$	–	4 1 0.5	A A A
P_{tot}	total power dissipation	$T_s = 90\text{ °C}$; note 1	–	500	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C

Note

1. T_s is the temperature at the soldering point of the cathode tab.

High-speed diode

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ELECTRICAL CHARACTERISTICS $T_j = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
V_F	forward voltage	see Fig.3		
		$I_F = 1\text{ mA}$	715	mV
		$I_F = 10\text{ mA}$	855	mV
		$I_F = 50\text{ mA}$	1	V
		$I_F = 150\text{ mA}$	1.25	V
I_R	reverse current	see Fig.5		
		$V_R = 25\text{ V}$	30	nA
		$V_R = 75\text{ V}$	1	μA
		$V_R = 25\text{ V}; T_j = 150\text{ °C}$	30	μA
		$V_R = 75\text{ V}; T_j = 150\text{ °C};$	50	μA
C_d	diode capacitance	$f = 1\text{ MHz}; V_R = 0;$ see Fig.6	1	pF
t_{rr}	reverse recovery time	when switched from $I_F = 10\text{ mA}$ to $I_R = 10\text{ mA};$ $R_L = 100\ \Omega;$ measured at $I_R = 1\text{ mA};$ see Fig.7	4	ns
V_{fr}	forward recovery voltage	when switched from $I_F = 10\text{ mA}; t_r = 20\text{ ns};$ see Fig.8	1.75	V

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-s}$	thermal resistance from junction to soldering point	note 1	120	K/W

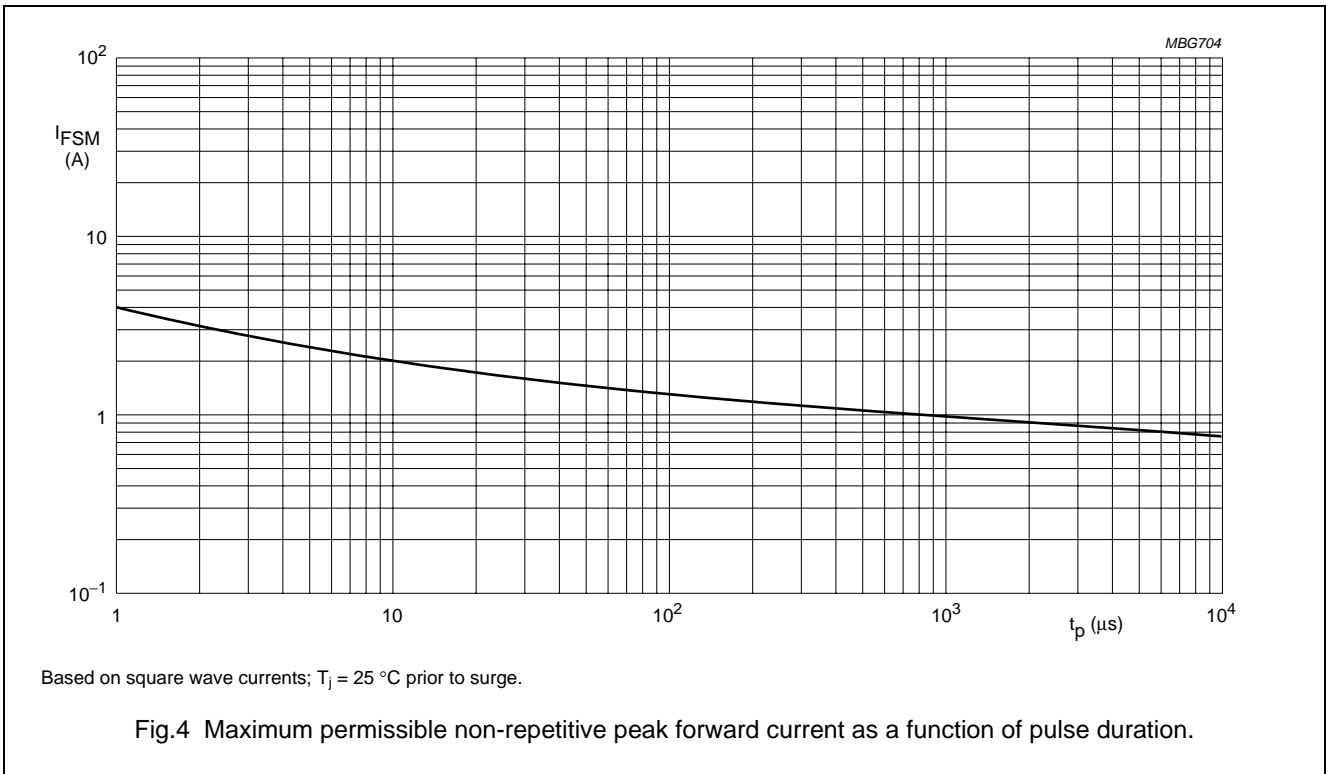
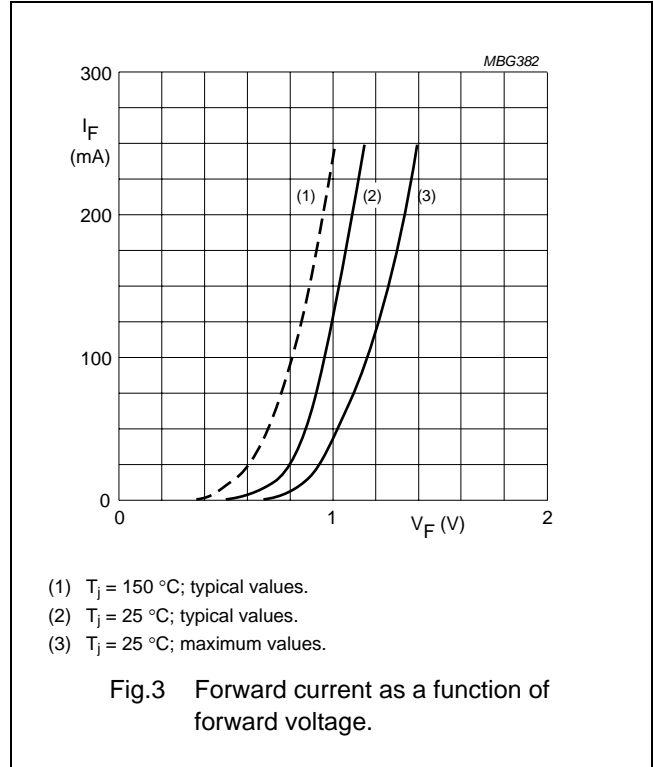
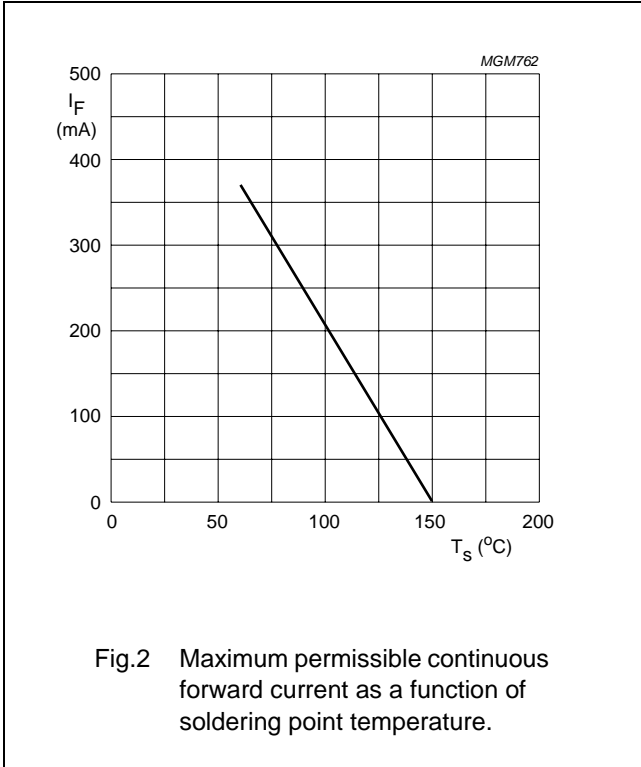
Note

1. Soldering point of the cathode tab.

High-speed diode

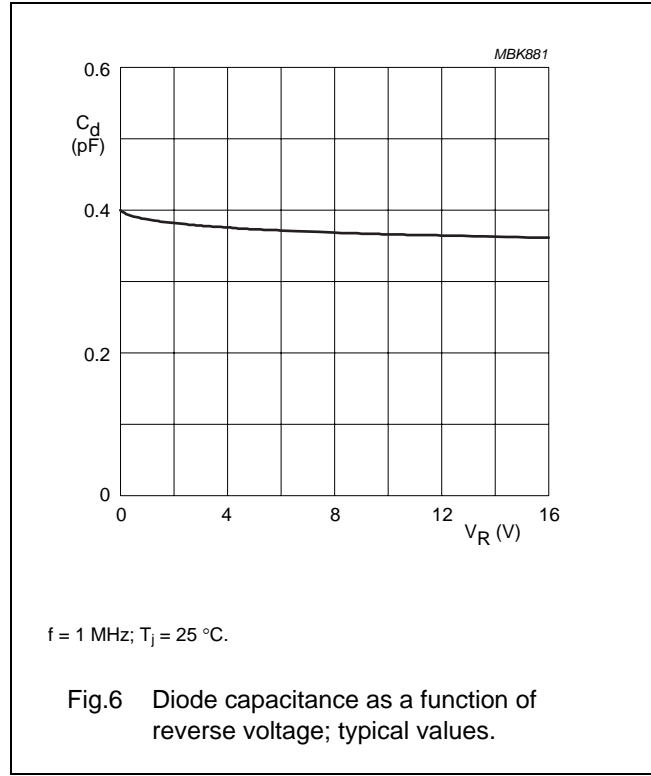
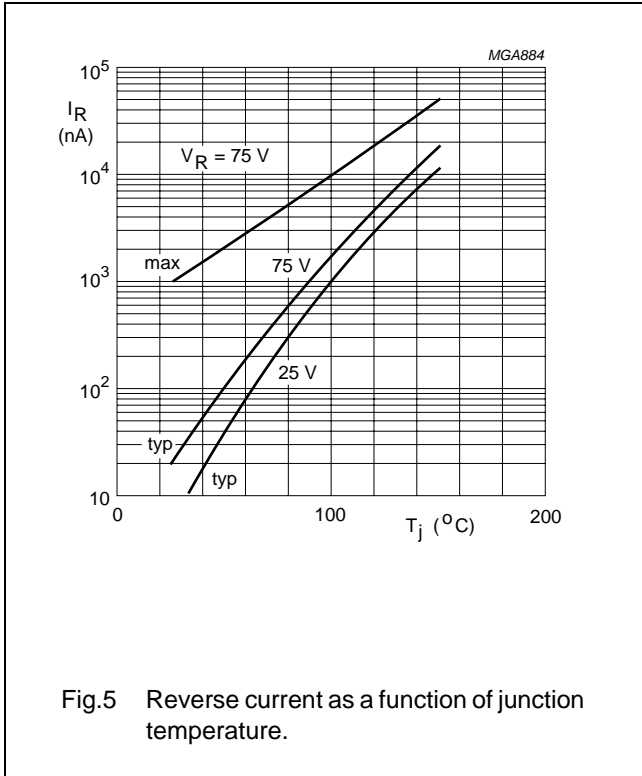
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GRAPHICAL DATA



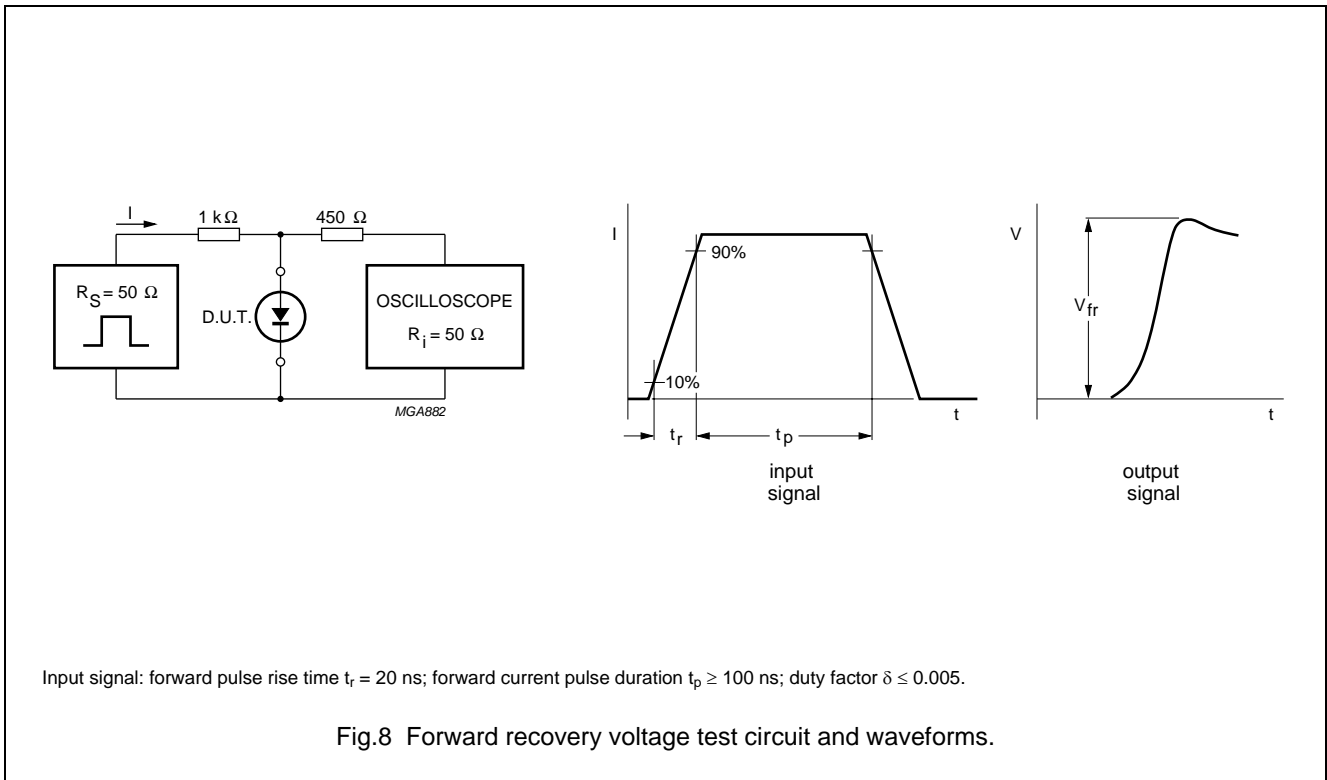
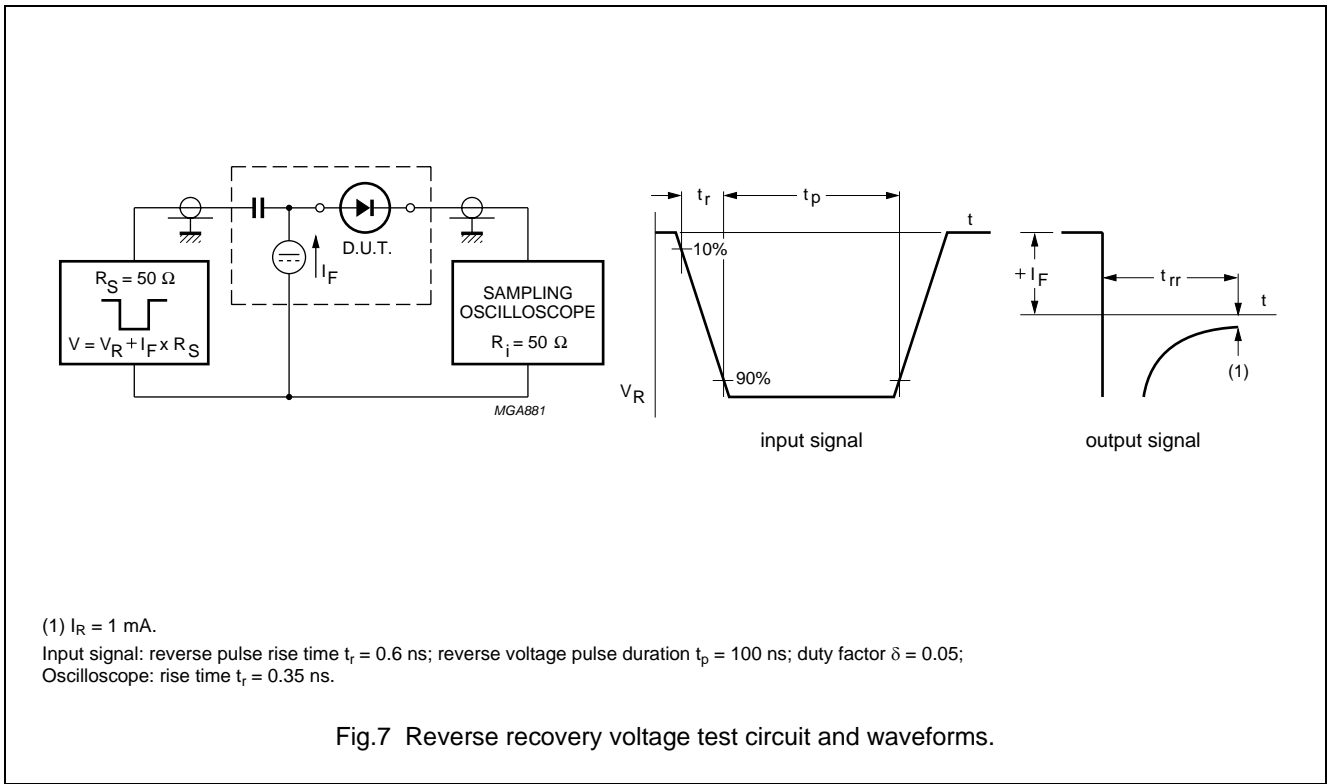
High-speed diode

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High-speed diode

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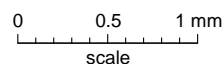
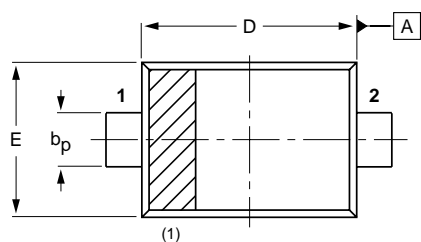
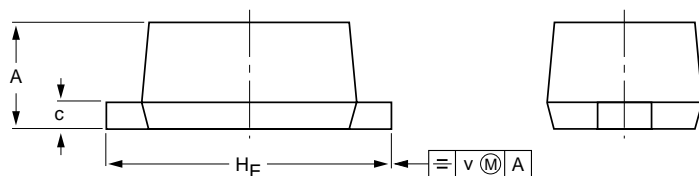
High-speed diode

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PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD523



DIMENSIONS (mm are the original dimensions)

UNIT	A	b _p	c	D	E	H _E	v
mm	0.65 0.58	0.34 0.26	0.17 0.11	1.25 1.15	0.85 0.75	1.65 1.55	0.1

Note

1. The marking bar indicates the cathode.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOD523			SC-79			-98-11-25- 02-12-13

High-speed diode

BAS516

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

1. Please consult the most recently issued document before initiating or completing a design.
2. The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

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